



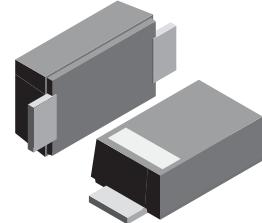
1N5819HW

SURFACE MOUNT SCHOTTKY BARRIER DIODE

VOLTAGE RANGE: 40V
CURRENT: 1.0 A

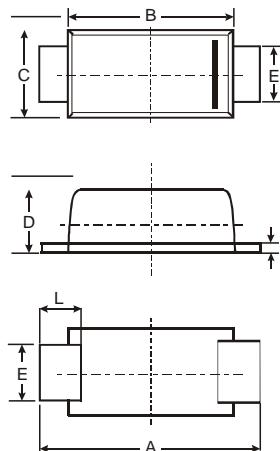
Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop



Mechanical Data

- Case: SOD-123FL plastic body over passivated junction
- Terminals : Plated axial leads,
- solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position : Any
- Weight:0.0007 ounce, 0.02 grams



SOD-123FL			
Dim	Min	Max	Typ
A	3.50	3.80	3.65
B	2.60	2.90	2.75
C	1.70	1.90	1.80
D	0.09	1.10	1.00
E	0.08	1.10	0.095
H	0.12	0.20	0.16
L	0.07	0.09	0.08

All Dimensions in mm

Maximum Ratings

@ $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	1N5819HW			Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWMM} V_R		40		V
RMS Reverse Voltage	$V_{R(RMS)}$		28		V
Average Rectified Output Current @ $T_L = 90^\circ\text{C}$	I_o		1.0		A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}		25		A
Power Dissipation (Note 2)	P_d		450		mW
Typical Thermal Resistance Junction to Ambient (Note 2)	R_{0JA}		222		$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}		-65 to +125		$^\circ\text{C}$

Electrical Characteristics

@ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	40	—	—	V	$I_R = 1.0\text{mA}$
Forward Voltage (Note 1)	V_F	—	—	0.320 0.450 0.750	V	$I_F = 0.1\text{A}$ $I_F = 1.0\text{A}$ $I_F = 3.0\text{A}$
Reverse Leakage Current (Note 1)	I_R	— — — — —	— — 10 1 15 1.5	1.0 50 2 75 3	mA mA μA mA μA mA	$V_R = 40\text{V}, T_A = 25^\circ\text{C}$ $V_R = 40\text{V}, T_A = 100^\circ\text{C}$ $V_R = 4\text{V}, T_A = 25^\circ\text{C}$ $V_R = 4\text{V}, T_A = 100^\circ\text{C}$ $V_R = 6\text{V}, T_A = 25^\circ\text{C}$ $V_R = 6\text{V}, T_A = 100^\circ\text{C}$
Total Capacitance	C_T	—	110	—	pF	$V_R = 4\text{V}, f = 1.0\text{MHz}$

Notes:

1. Short duration pulse test used to minimize self-heating effect.
2. Device mounted on FR-4 PC Board, 2"x2", 2 oz. Copper, single sided, Cathode pad dimensions 0.75"x1.0", Anode pad dimensions 0.25"x1.0".

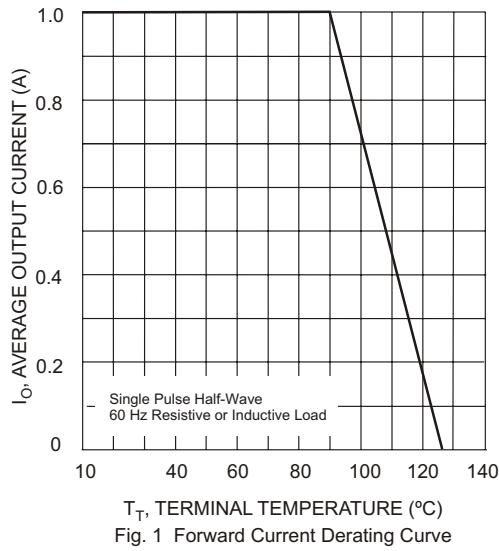


Fig. 1 Forward Current Derating Curve

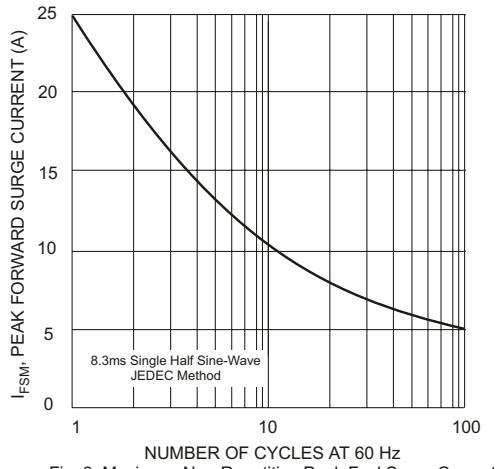


Fig. 3 Maximum Non-Repetitive Peak Fwd Surge Current

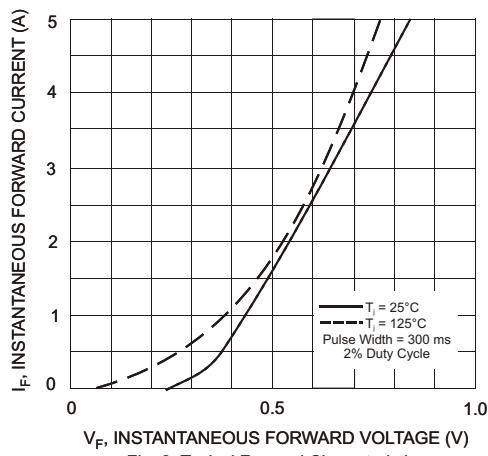


Fig. 2 Typical Forward Characteristics

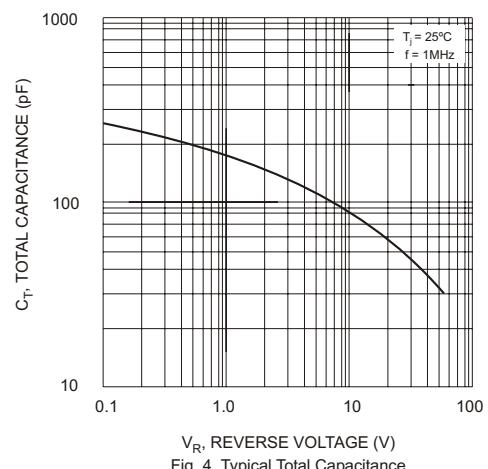


Fig. 4 Typical Total Capacitance

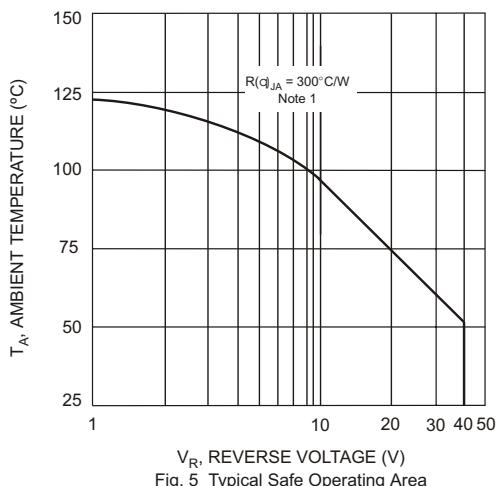


Fig. 5 Typical Safe Operating Area

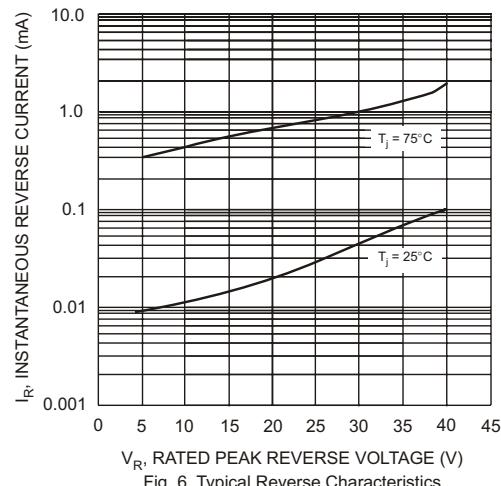


Fig. 6 Typical Reverse Characteristics